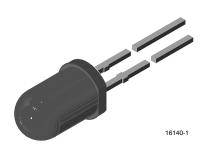
Vishay Semiconductors



Silicon PIN Photodiode, RoHS Compliant



DESCRIPTION

BPV10NF is a PIN photodiode with high speed and high radiant sensitivity in black, T-1¾ plastic package with daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

FEATURES

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

· Leads with stand-off

• Radiant sensitive area (in mm2): 0.78

· High radiant sensitivity

 Daylight blocking filter matched with 870 nm to 950 nm emitters

• High bandwidth: > 100 MHz at V_R = 12 V

• Fast response times

• Angle of half sensitivity: $\varphi = \pm 20^{\circ}$

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSFFxxxx series IR emitters

| PRODUCT SUMMARY | | | | |
|-----------------|----------------------|----------------|-----------------------|--|
| COMPONENT | I _{ra} (mA) | φ (deg) | λ _{0.5} (nm) | |
| BPV10NF | 60 | ± 20 | 790 to 1050 | |

Note

Test condition see table "Basic Characteristics"

| ORDERING INFORMATION | | | | |
|----------------------|-----------|------------------------------|--------------|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | |
| BPV10NF | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|-------------------------------------|--|-------------------|---------------|------|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | |
| Reverse voltage | | V _R | 60 | V | |
| Power dissipation | T _{amb} ≤ 25 °C | P _V | 215 | mW | |
| Junction temperature | | Tj | 100 | °C | |
| Operating temperature range | | T _{amb} | - 40 to + 100 | °C | |
| Storage temperature range | | T _{stg} | - 40 to + 100 | °C | |
| Soldering temperature | $t \le 5 \text{ s}, 2 \text{ mm from body}$ | T _{sd} | 260 | °C | |
| Thermal resistance junction/ambient | Connected with Cu wire, 0.14 mm ² | R _{thJA} | 350 | K/W | |

Note

T_{amb} = 25 °C, unless otherwise specified





ROHS



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| BASIC CHARACTERISTICS | | | | | | |
|--|---|-------------------|------|-----------------------|------|---------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | I _F = 50 mA | V_{F} | | 1.0 | 1.3 | V |
| Breakdown voltage | I _R = 100 μA, E = 0 | V _(BR) | 60 | | | V |
| Reverse dark current | V _R = 20 V, E = 0 | I _{ro} | | 1 | 5 | nA |
| Diode capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _D | | 11 | | pF |
| Open circuit voltage | $E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm}$ | Vo | | 450 | | mV |
| Short circuit current | $E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm}$ | I _K | | 50 | | μΑ |
| Reverse light current | $E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm},$ $V_R = 5 \text{ V}$ | I _{ra} | | 55 | | μΑ |
| | $E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \ V_R = 5 \text{ V}$ | I _{ra} | 30 | 60 | | μΑ |
| Temperature coefficient of I _{ra} | $E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm},$ $V_R = 5 \text{ V}$ | TK _{Ira} | | - 0.1 | | %/K |
| Absolute spectral sensitivity | $V_R = 5 \text{ V}, \ \lambda = 870 \text{ nm}$ | s(λ) | | 0.55 | | A/W |
| Angle of half sensitivity | | φ | | ± 20 | | deg |
| Wavelength of peak sensitivity | | λ_{p} | | 940 | | nm |
| Range of spectral bandwidth | | λ _{0.5} | | 790 to 1050 | | nm |
| Quantum efficiency | $\lambda = 950 \text{ nm}$ | η | | 70 | | % |
| Noise equivalent power | $V_R = 20 \text{ V}, \ \lambda = 950 \text{ nm}$ | NEP | | 3 x 10 ⁻¹⁴ | | W/√Hz |
| Detectivity | $V_R = 20 \text{ V}, \ \lambda = 950 \text{ nm}$ | D* | | 3 x 10 ¹² | | cm√Hz/W |
| Rise time | $V_R = 50 \text{ V}, R_L = 50 \Omega, \lambda = 820 \text{ nm}$ | t _r | | 2.5 | | ns |
| Fall time | $V_R = 50 \text{ V}, R_L = 50 \Omega, \lambda = 820 \text{ nm}$ | t _f | | 2.5 | | ns |

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

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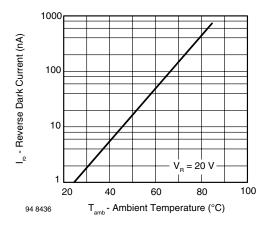


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

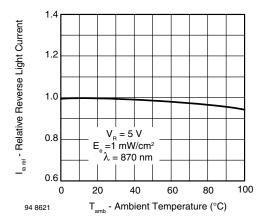


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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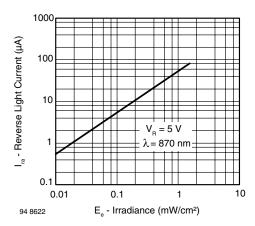


Fig. 3 - Reverse Light Current vs. Irradiance

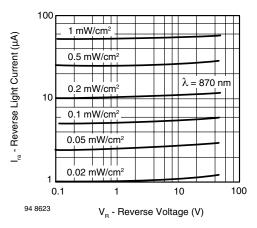


Fig. 4 - Reverse Light Current vs. Reverse Voltage

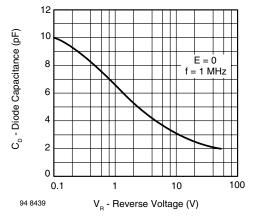


Fig. 5 - Diode Capacitance vs. Reverse Voltage

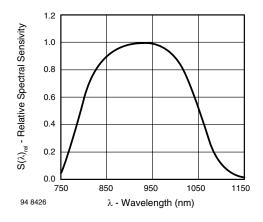


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

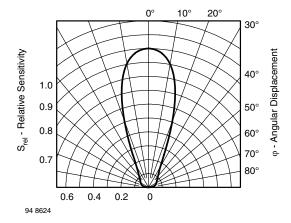
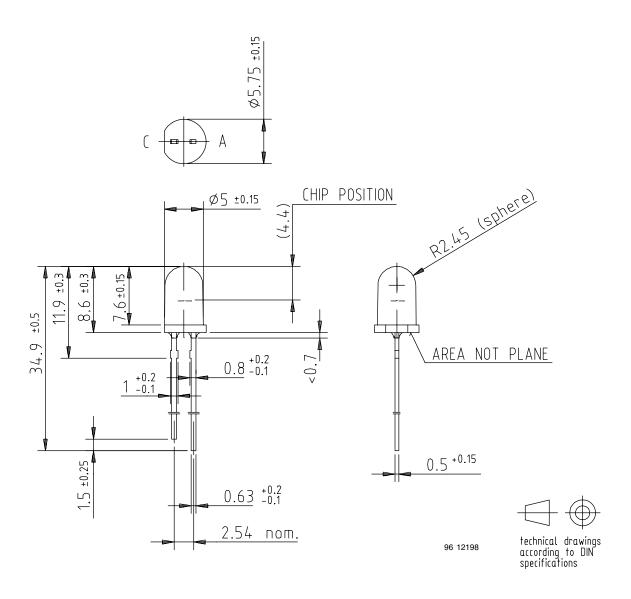


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters







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